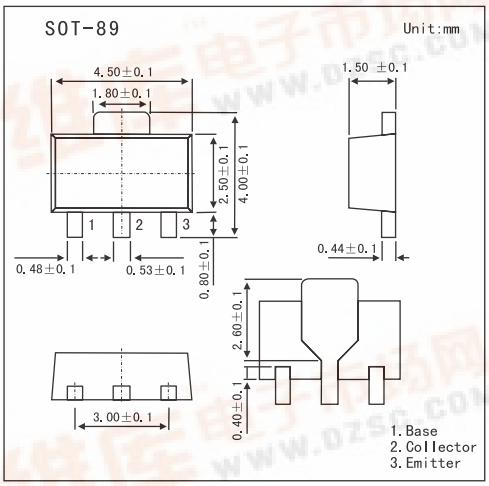
PNP Silicon Epitaxia

2SA1463



■ Features

- ● High speed,high voltage switching.
- ●Low Collector Saturation Voltage

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-60	V
Collecto to emitter voltage	V_{CEO}	-45	V
Emitter to base voltage	V_{EBO}	-5.0	V
Collector current(DC)	I_C	-1.0	A
Collector current(Pulse)*	I_C	-2.0	A
Total power dissipation	P_T	20	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

*.pw≤10 ms,Duty Cycle≤50%

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CES}	V_{CE} = -45V, R_{BE}=0			-0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -4V, I_C=0			-0.5	μA
DC current gain *	h_{FE1}	V_{CE} = -10V , I_C = -50mA	60		200	
	h_{FE2}	V_{CE} = -10V , I_C = -500mA	60			
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = -500mA , I_B = -50mA		-0.26	-0.6	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C = -500mA , I_B = -50mA		-0.98	-1.2	V
Gain bandwidth product	f_T	V_{CE} = -10V , I_E = 100mA	300	400		MHz
Output capacitance	C_{ob}	V_{CB} = -10V , I_E = 0 , f = 1.0MHz		11	25	pF
Turn-on time	t_{on}	I_C = -500mA , I_{B1} = I_{B1} = -50mA		25	40	ns
Storage time	t_{stg}			46	70	ns
Turn-off time	t_{off}			62	100	ns

* Pulse test: tp ≤ 350 μs; d ≤ 0.02.

■ h_{FE} Classification

Marking	1L	1K
h_{FE}	60～120	100～200